

From: [Key, Cara M](#)
To: [Alan Telecky](#)
Subject: Re: Publicly available dissertations
Date: Thursday, February 15, 2024 12:02:48 PM
Attachments: [image.png](#)
[f4752m006.json](#)
[qr46r2982.json](#)
[rf55zb08z.json](#)

[WARNING] This email originated from an external sender and should be treated with extra caution.

Hi Alan,

These three dissertations were all originally submitted to the IR when the IR was using its previous software platform – it was migrated to the current one in 2017. Unfortunately the record of prior embargo dates wasn't retained through the migration, so I don't have that information for anything earlier than 2017 and I can't confirm either way. You're welcome to review – I attached the full database record (except the full text field, just for readability's sake) for each of those items.

As far as the submission versus available dates: The approval process these days is usually quicker than 2 months but is still the same basic workflow as far as I know. This is what you'll see under "Additional Information / Description.Provenance" in the full database record, which was transferred over from the original DSpace system.

- description.provenance : Approved for entry into archive by Julie Kurtz(julie.kurtz@oregonstate.edu) on 2012-06-07T20:14:49Z (GMT) No. of bitstreams: 1 TeleckyAlanJ2012.pdf: 4240401 bytes, checksum: 476d833292a780c24160af7c96869ea0 (MD5)
- description.provenance : Submitted by Alan Telecky (teleckya@onid.orst.edu) on 2012-05-21T21:56:33Z No. of bitstreams: 1 TeleckyAlanJ2012.pdf: 4240401 bytes, checksum: 476d833292a780c24160af7c96869ea0 (MD5)
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The student submits their thesis or dissertation and it enters a review queue. A Graduate School staff member reviews and approves the work (possibly going through a round or two of formatting edits or similar) – at that time, it was Julie Kurtz. Then a Library/Repository staff member reviews the final details and publishes it – in this case, Laura Wilson was the final approver. Publishing creates that Date Available timestamp, though it doesn't necessarily mean it was fully public, just that it had fully completed the approval process. The embargo functionality was handled separately from the approval workflow, and didn't create the same provenance trail.

Sorry it isn't the answer you're looking for, but please let me know if I can be of further help.

Best,
Cara

Cara Key
Digital Repository Librarian
Library Information Technology
The Valley Library
Oregon State University
cara.key@oregonstate.edu
C: (336) 707-1672
she/her

From: Alan Telecky <atelecky@inpria.com>
Date: Thursday, February 15, 2024 at 07:54
To: Key, Cara M <cara.key@oregonstate.edu>
Subject: Publicly available dissertations

You don't often get email from atelecky@inpria.com. [Learn why this is important](#)

[This email originated from outside of OSU. Use caution with links and attachments.]

Hi Cara,

I have a question about the dates that a couple of dissertations from OSU were made publicly available. The OSU library links to each dissertation are here:

https://ir.library.oregonstate.edu/concern/graduate_thesis_or_dissertations/rf55zb08z?locale=en

https://ir.library.oregonstate.edu/concern/graduate_thesis_or_dissertations/qr46r2982?locale=en

https://ir.library.oregonstate.edu/concern/graduate_thesis_or_dissertations/f4752m006?locale=en

Of course, I can see the entries under Date Available:



but I'm curious if any of these dissertations were under embargo for any amount of time? I had thought that mine at least had been embargoed, but maybe not according to the displayed Date Available. From what I can tell, it looks like these were all

submitted and then made available a short while (~1-2 mo.) after submission.

Can you confirm if these dissertations were under any embargo at any point?

And sorry if you are not the right person for this question. If you are not, could you please point me to the correct contact?

Many thanks for your help!

Cheers,
Alan

Alan J. Telecky, PhD
Inpria Corporation
1100 NE Circle Blvd, Suite 360
Corvallis OR, 97330
Phone: (541) 243-2310

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ATTACHMENT 1

(image.png)

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ATTACHMENT 2

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Polycondensation behaviors of aqueous Al+3 and PO4 +3 are manipulated in the
deposition of atomically smooth amorphous aluminum oxide phosphate (AlPO)
dielectric films. AlPO gate dielectrics with performance parameters not previously
demonstrated via solution are integrated in thin-film transistors (TFTs). Simple
zinc-ammine coordination chemistries enable low-temperature ink-jet printing of ZnO
semiconductor films. Solution deposited ZnO films processed at low temperatures are
integrated with AlPO dielectrics in high-performance TFTs. Discrete group 13
heterometallic hydroxo clusters are developed as aqueous precursors for InGaO3
semiconductor films. Insights from these polynuclear clusters are utilized in the
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Polycondensation behaviors of aqueous Al+3 and PO4 +3 are manipulated in the
deposition of atomically smooth amorphous aluminum oxide phosphate (AlPO)
dielectric films. AlPO gate dielectrics with performance parameters not previously
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zinc-ammine coordination chemistries enable low-temperature ink-jet printing of ZnO
semiconductor films. Solution deposited ZnO films processed at low temperatures are
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heterometallic hydroxo clusters are developed as aqueous precursors for InGaO3
semiconductor films. Insights from these polynuclear clusters are utilized in the

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synthesis of aqueous precursors for amorphous InGaZnO₄ semiconductor films. These channels are similarly integrated with solution processed AlPO dielectrics on glass substrates, thereby demonstrating the potential for solution processed oxide macroelectronics.\$0"],

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unsuitably. An inorganic resist has been developed that exhibits excellent performance in these important metrics, as well as others which are required of state-of-the-art resists. This inorganic resist has shown sensitivity to a variety of modern exposure sources. The patterning chemistry which has been developed is adaptable to a large number of metal oxides. Direct pattern of metal oxides also offers potential for the modification of the material through solution based or solid state methods in order to access a variety of material properties not found in the initial metal oxide."],

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This metal oxide can then be considered an inorganic \r\nresist. Inorganic resists have proven to offer a higher resolution and etch resistance \r\nthan a comparable polymer resist. The work presented here represents efforts to \r\ndevelop directly patterned metal oxides that exhibits these desired resist properties, but \r\nwhich also competes with polymer resist in terms of sensitivity, the one area inorganic \r\nresists have always performed unsuitably. An inorganic resist has been developed that \r\nexhibits excellent performance in these important metrics, as well as others which are required of state-of-the-art resists. This inorganic resist has shown sensitivity to a \r\nvariety of modern exposure sources. The patterning chemistry which has been \r\ndeveloped is adaptable to a large number of metal oxides. Direct pattern of metal oxides \r\nalso offers potential for the modification of the material through solution based or \r\nsolid state methods in order to access a variety of material properties not found in the \r\ninitial metal oxide.\$0"],

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with a metal oxide that can be directly patterned. \r\n Solution deposition of metal
oxides allows the possibility of depositing materials that \r\n are responsive to
traditional lithographic patterning methods. A directly patterned \r\n resist can
be integrated into devices with less difficulty. It is also possible, with a
\r\n directly patterned metal oxide, to consider this material also as a resist for
the \r\n patterning of another material. This metal oxide can then be considered an
inorganic \r\n resist. Inorganic resists have proven to offer a higher resolution
and etch resistance \r\n than a comparable polymer resist. The work presented here
represents efforts to \r\n develop directly patterned metal oxides that exhibits
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terms of sensitivity, the one area inorganic \r\n resists have always performed

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unsuitably. An inorganic resist has been developed that exhibits excellent performance in these important metrics, as well as others which are required of state-of-the-art resists. This inorganic resist has shown sensitivity to a variety of modern exposure sources. The patterning chemistry which has been developed is adaptable to a large number of metal oxides. Direct pattern of metal oxides also offers potential for the modification of the material through solution based or solid state methods in order to access a variety of material properties not found in the initial metal oxide."],

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